36.0 - 40.0 GHz HEMT Low Noise Amplifier

M. Sholley, J. Berenz, A. Nichols, K. Nakano, R. Sawires and J. Abell. "36.0 - 40.0 GHz HEMT Low Noise Amplifier." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 555-558.

This paper describes the design and development of a multistage low noise High Electron Mobility Transistor (HEMT) amplifier that exhibits state-of-the-art performance over the frequency range of 36-40 GHz. The amplifier utilizes a series of three single ended stages that are each designed around TRW's HEMT device. Typical performance to date has been 15-17 dB gain with an associated noise figure of 4.0 to 4.6 dB.

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